## Surface Mount

# **Monolithic Amplifier**

## DC-4 GHz

#### **Product Features**

- InGaP HBT microwave amplifier
- Miniature SOT-89 package
- Frequency range, DC to 4 GHz
- Output power, 17.5 dBm typ.
- Excellent package for heat dissipation, exposed metal bottom
- Low thermal resistance for high reliability
- Aqueous washable
- Protected by US Patent 6,943,629

#### **Typical Applications**

- Cellular
- PCS
- · Communication receivers & transmitters



CASE STYLE: DE782 PRICE: \$1.49 ea. QTY. (30)

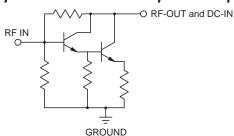
+ RoHS compliant in accordance with EU Directive (2002/95/EC)

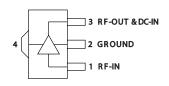
The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

#### **General Description**

Gali:4+ (RoHS compliant) is a wideband amplifier offering high dynamic range. Lead finish is SnAgNi. It has repeatable performance from lot to lot, and is enclosed in a SOT-89 package. It uses patented Transient Protected Darlington configuration and is fabricated using InGaP HBT technology. Expected MTBF is 4,000 years at 85°C case temperature. Gali, 4+ is designed to be rugged for ESD and supply switch-on transients.

#### simplified schematic and pin description





Function	Pin Number	Description
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit".
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.

 **□ Mini-Circuits** 

For detailed performance spec & shopping online see web site



## Electrical Specifications at 25°C and 65mA, unless noted

Parameter		Min.	Тур.	Max.	Units
Frequency Range*		DC		4	GHz
Gain	f=0.1 GHz		14.4		dB
	f=1 GHz		14.1		
	f=2 GHz	11	13.5		
	f=3 GHz		12.9		
	f=4 GHz		12.5		
	f=6 GHz		13.1		
Input Return Loss	f= DC to 3 GHz		21		dB
	f= 3 to 4 GHz		21		
Output Return Loss	f= DC to 3 GHz		15.5		dB
	f= 3 to 4 GHz		11.5		
Output Power @ 1 dB compression	f=1 GHz	16.0	17.5		dBm
Output IP3	f=1 GHz		34		dBm
Noise Figure	f=1 GHz		4.0		dB
Recommended Device Operating Current			65		mA
Device Operating Voltage		4.2	4.6	5.5	V
Device Voltage Variation vs. Temperature at 65 mA			-3.1		mV/°C
Device Voltage Variation vs. Current at 25°C		10.0		mV/mA	
Thermal Resistance, junction-to-case <sup>1</sup>			93		°C/W

<sup>\*</sup>Guaranteed specification DC-4 GHz. Low frequency cut off determined by external coupling capacitors.

## **Absolute Maximum Ratings**

Parameter	Ratings	
Operating Temperature*	-45°C to 85°C	
Storage Temperature	-65°C to 150°C	
Operating Current	85mA	
Input Power	20dBm	

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.

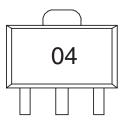
<sup>1</sup>Case is defined as ground leads.

\*Based on typical case temperature rise 4°C above ambient.



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#### **Product Marking**



#### **Additional Detailed Technical Information**

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: DF782

Plastic package, exposed paddle, lead finish: tin/silver/nickel

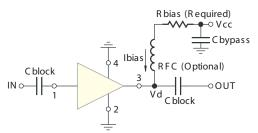
Tape & Reel: F55

Suggested Layout for PCB Design: PL-019

Evaluation Board: TB-409-4+

**Environmental Ratings: ENV08T2** 

#### **Recommended Application Circuit**



Test Board includes case, connectors, and components (in bold) soldered to  $\ensuremath{\mathsf{PCB}}$ 

R BIAS				
Vcc	"1%" Res. Values (ohms) for Optimum Biasing			
7	38.3			
8	52.3			
9	66.5			
10	80.6			
11	95.3			
12	110			
13	127			
14	143			
15	158			
16	174			
17	187			
18	205			
19	221			
20	237			

Mini-Circuits

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IFIRF MICROWAVE COMPONENTS



#### **ESD Rating**

Human Body Model (HBM): Class 1A (250v to 500v) in accordance with ANSI/ESD STM 5.1 - 2001

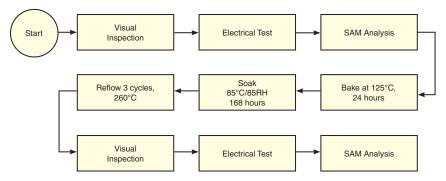
Machine Model (MM): Class M1 (< 100v) in accordance with ANSI/ESD STM 5.2 - 1999

### **MSL** Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDECJ-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	45 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	45 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	45 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	45 units

#### **MSL Test Flow Chart**



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